Package • Code

TO-92B-B1 • Pin Name

1. Emitter

2SB0621

Silicon PNP epitaxial planar type

For low-frequency driver amplification Complementary to SD0592

Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- High transition frequency f_T

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	-30	V
Collector-emitter voltage (Base open)	V _{CEO}	-25	V
Emitter-base voltage (Collector open)	V _{EBO}	-5	V
Collector current	I _C	-1	A
Peak collector current	I _{CP}	-1.5	A
Collector power dissipation	P _C	750	mW
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

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Parameter	Symbol	Conditions	Min	Тур	Max	Unit				
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \mu {\rm A}, I_{\rm E} = 0$	-30			V				
Collector-emitter voltage (Base open)	V _{CEO}	$I_{c} = -2 \text{ mA}, I_{B} = 0$	-25			V				
Emitter-base voltage (Collector open)	V _{EBO}	I _E =-10 μA, I _C =0	-5			V				
Collector-base cutoff current (Emitter open)	Ісво	$V_{CB} = -20$ V $I_E = 0$			- 0.1	μΑ				
Forward current transfer ratio	h _{FE1} *	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$	85		340					
	h _{FE2}	$V_{CE} = -5 X I_C = -1 A$	50							
Collector-emitter saturation voltage	V _{CE(sat})	$I_{\rm C} = -500 \text{ mA}, I_{\rm B} = -50 \text{ mA}$		- 0.2	-0.4	V				
Base-emitter saturation voltage	VBE(sat)	$I_{\rm C} = -500 \text{ mA}, I_{\rm B} = -50 \text{ mA}$		- 0.85	-1.2	V				
Transition frequency	f _T	$V_{CB} = -10$ V, $I_E = 50$ mA, $f = 200$ MHz		200		MHz				
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		20	30	pF				
(Common base, input open circuited)	Cob	$\left \begin{array}{c} \mathbf{v}_{\mathrm{CB}} = -\mathbf{i}_{\mathrm{O}} \mathbf{v}, \mathbf{i}_{\mathrm{E}} = 0, \mathbf{i} = \mathbf{i}_{\mathrm{O}} \mathbf{v}_{\mathrm{O}} \mathbf{i}_{\mathrm{E}} \right $		20	50	pr				

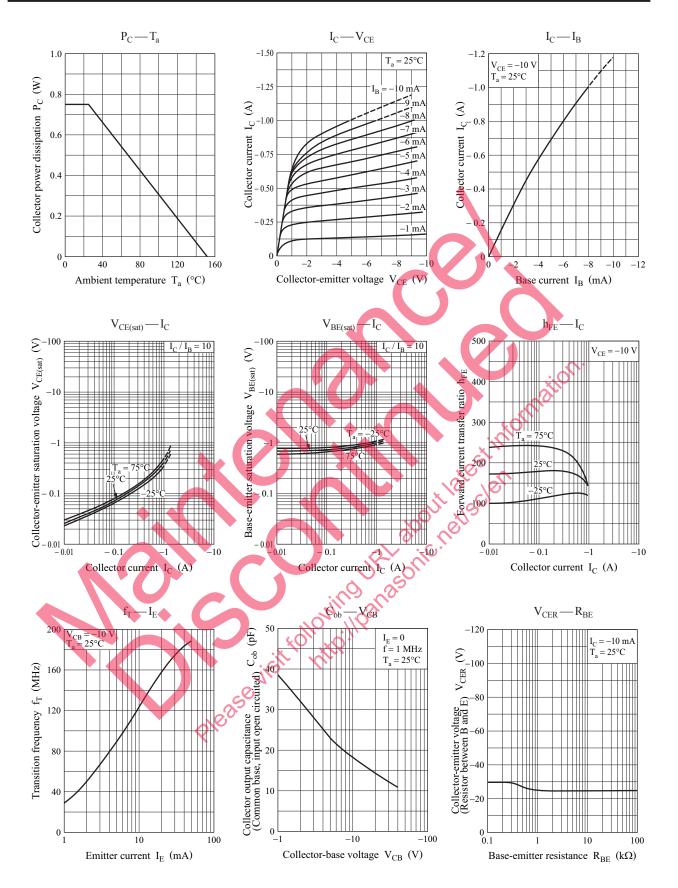
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

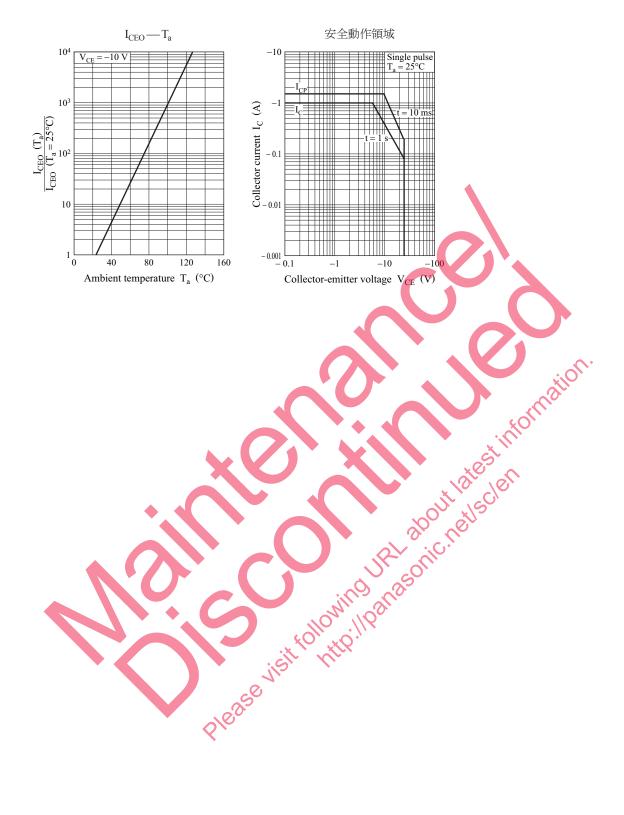
Rank	Q	R	S
$h_{\rm FE1}$	85 to 170	120 to 240	170 to 340

2SB0621

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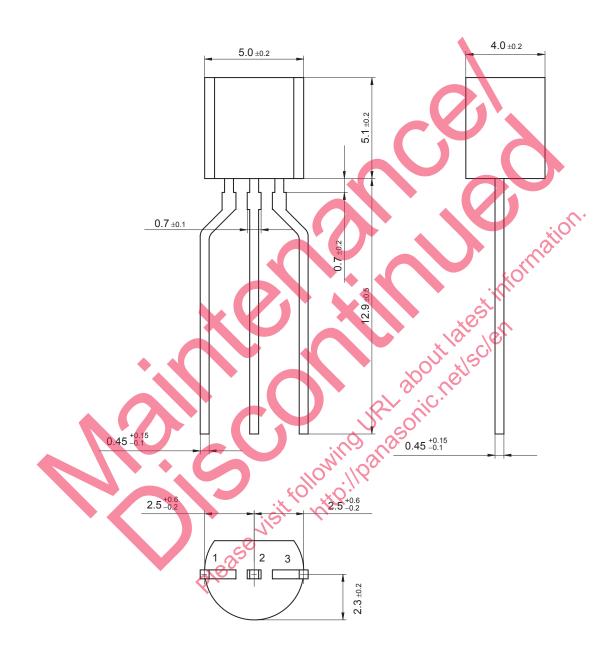
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TO-92-B1

Unit: mm



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